## We claim:

1. A device for mounting a substrate to be coated, comprising:

a susceptor for supporting a substrate;

said susceptor including an insert having a surface; and

a metal carbide layer of a given thickness forming at least a portion of said surface.

- 2. The device according to claim 1, wherein said insert includes a plurality of tiles, each of said tiles being provided for a respective substrate.
- 3. The device according to claim 2, wherein each of said tiles is formed with a depression for the respective substrate.
- 4. The device according to claim 1, wherein said insert includes a graphite core, said metal carbide layer covers said graphite core.
- 5. The device according to claim 1, wherein said insert includes a metal core, said metal carbide layer covers said metal core.



- 6. The device according to claim 1, wherein said given thickness of said metal carbide layer decreases with an increasing distance from the substrate.
- 7. The device according claim 1, wherein said metal carbide layer includes tantalum carbide.
- 8. The device according to claim 1, wherein said metal carbide layer includes niobium carbide.
- 9. The device according to claim 1, wherein said metal carbide layer includes tungsten carbide.
- 10. The device according to claim 1, wherein said metal carbide layer includes molybdenum carbide.

12. A method for producing an insert for a susceptor, the method which comprises:

producing a metallic preform;

embedding the metallic preform in a carbon-containing powder;

heating the metallic preform and the carbon-containing powder to an elevated temperature for providing a heat-treated preform;

hard processing the heat-treated preform for providing a hardprocessed preform having a surface layer made of a metal carbide; and

disposing the hard-processed preform as an insert on a susceptor.

- The method according to claim 11, which comprises performing the heating step under an elevated pressure.
- The method according to claim 11, which comprises heating 13. the metallic preform and the carbon-containing powder to the elevated temperature of between 1500°C and 2000°C.
- The method according to claim 11, which comprises using a silicon carbide powder as the carbon-containing powder.

